ON Semiconductor

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Single 3-Input NAND Gate

NL17SZ10

The NL17SZ10 is a single 3-input NAND Gate in tiny footprint packages.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.4 ns t_{PD} at $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Chip Complexity < 100 FETs
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

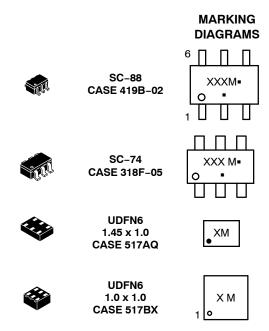


Figure 1. Logic Symbol



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XX, XXX = Specific Device Code M = Date Code*

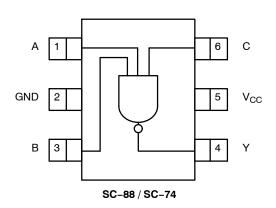
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.



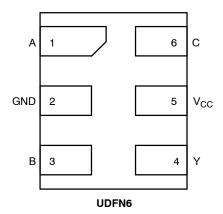


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

Pin	Function
1	А
2	GND
3	В
4	Υ
5	V _{CC}
6	С

FUNCTION TABLE $(Y = \overline{ABC})$

	Output		
Α	В	С	Υ
Х	Х	L	Н
Х	L	Х	Н
L	Х	Х	Н
Н	Н	Н	L

H = HIGH Logic Level L = LOW Logic Level X = Either LOW or HIGH Logic Level

MAXIMUM RATINGS

Symbol	Characteris	Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	٧
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
l _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground	±100	mA	
T _{STG}	Storage Temperature Range	-65 to +150	°C	
T_L	Lead Temperature, 1 mm from Case for 10 s	ecs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P _D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics			Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	Т,	4 = 25°(C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input		1.65 to 1.95	0.65 V _{CC}	_	_	0.65 V _{CC}	_	٧
	Voltage		2.3 to 5.5	0.70 V _{CC}	-	-	0.70 V _{CC}	-	
V _{IL}	Low-Level Input		1.65 to 1.95	-	-	0.35 V _{CC}	-	0.35 V _{CC}	V
	Voltage		2.3 to 5.5	-	-	0.30 V _{CC}	-	0.30 V _{CC}	
V _{OH}	High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -100 µA I _{OH} = -4 mA I _{OH} = -8 mA I _{OH} = -16 mA I _{OH} = -24 mA I _{OH} = -32 mA	1.65 to 5.5 1.65 2.3 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.7 2.5 4.0	- - - - -	V _{CC} - 0.1 1.29 1.9 2.4 2.3 3.8	- - - - -	V
V _{OL}	Low-Level Output Voltage	$\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 100 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \\ &I_{OL} = 16 \text{ mA} \\ &I_{OL} = 24 \text{ mA} \\ &I_{OL} = 32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 3.0 3.0 4.5	- - - -	- 0.08 0.2 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.55 0.55	- - - -	0.1 0.24 0.3 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	_	-	±0.1	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	_	10	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	_	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

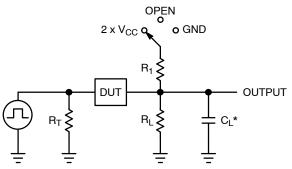
AC ELECTRICAL CHARACTERISTICS

			V _{CC}	T,	_A = 25°	С	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
t _{PLH,}	t _{PLH,} Propagation Delay, (A or B or C) to Y (Figures 3 and 4)	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	1.65 to 1.95	-	7.0	17.5	-	18.0	ns
₹PHL		$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	2.3 to 2.7	-	3.0	10.5	-	11.0	
,	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	3.0 to 3.6	-	2.4	7.5	-	8.0		
		$R_L = 500 \Omega$, $C_L = 50 pF$		-	2.9	8.5	-	9.0	
		$R_L = 1 \text{ M}\Omega$, $C_L = 15 \text{ pF}$	4.5 to 5.5	-	2.0	5.5	-	6.0	
		$R_L = 500 \Omega$, $C_L = 50 pF$		_	2.4	7.5	-	8.0	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C _L , pF	R_L , Ω	R ₁ , Ω	
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table			
t _{PLZ} / t _{PZL}	2 x V _{CC}	50	500	500	
t _{PHZ} / t _{PZH}	GND	50	500	500	

X = Don't Care

C_L includes probe and jig capacitance

 R_T is Z_{OUT} of pulse generator (typically 50 Ω)

f = 1 MHz

Figure 3. Test Circuit

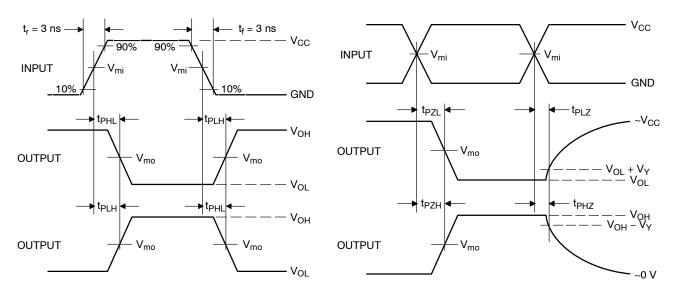


Figure 4. Switching Waveforms

		V _m		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

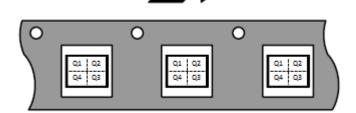
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL17SZ10DFT2G (In Development)	SC-88	TBD	Q4	3000 / Tape & Reel
NL17SZ10DBVT1G	SC-74	AQ	Q4	3000 / Tape & Reel
NL17SZ10MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
NL17SZ10MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

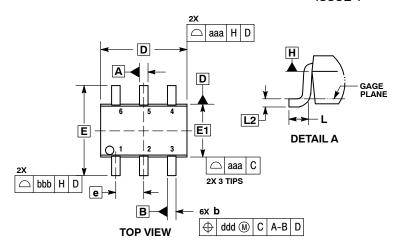
Direction of Feed

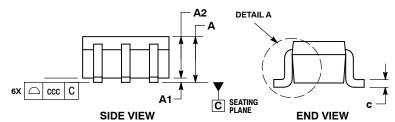


PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE Y**





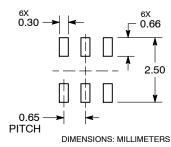
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION

- DIMENSION 5 DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN
 EXCESS OF DIMENSION 5 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

	MIL	LIMETE	RS		INCHES	3
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BS	С	0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15 BS	C		0.006 BS	SC
aaa	0.15				0.006	
bbb	0.30				0.012	
ccc	0.10			0.004		
ddd		0.10			0.004	

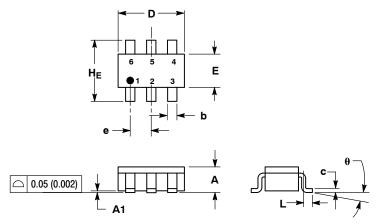
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

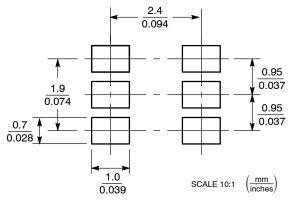
SC-74 CASE 318F-05 **ISSUE N**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.
 4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.985	0.95	11.05	0.084	0.037	0.10241
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ		-			-	

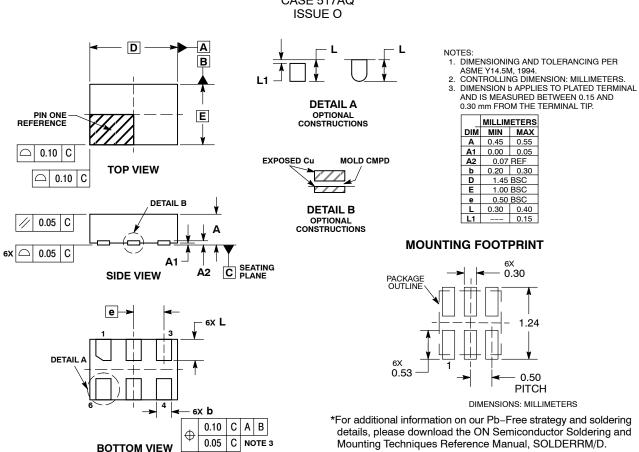
SOLDERING FOOTPRINT*



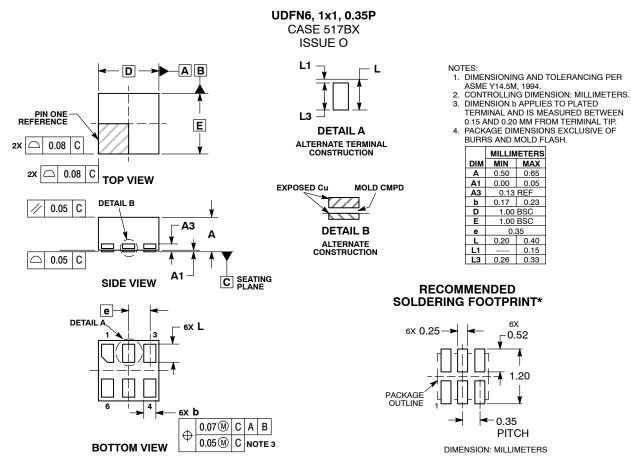
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P CASE 517AQ



PACKAGE DIMENSIONS



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NLX1G11AMUTCG NLX1G97MUTCG 74LS38 74LVC32ADTR2G MC74HCT20ADTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G
NLV74HC02ADR2G 74HC32S14-13 74LS133 74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7
NLV74HC08ADTR2G NLV74HC14ADR2G NLV74HC20ADR2G NLX2G86MUTCG 5962-8973601DA 74LVC2G02HD4-7
NLU1G00AMUTCG 74LVC2G32RA3-7 74LVC2G00HD4-7 NL17SG02P5T5G 74LVC2G00HK3-7 74LVC2G86HK3-7
NLX1G99DMUTWG NLVVHC1G00DFT2G NLVHC1G08DFT2G NLV7SZ57DFT2G NLV74VHC04DTR2G NLV27WZ86USG
NLV27WZ00USG NLU1G86CMUTCG NLU1G08CMUTCG NL17SZ32P5T5G NL17SZ00P5T5G NL17SH02P5T5G 74AUP2G00RA3-7
NLV74HC02ADTR2G NLX1G332CMUTCG NL17SG86P5T5G NL17SZ05P5T5G